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Nota di contenuto	Intro -- Supervisor's Foreword -- Acknowledgments -- Contents -- Parts of This Thesis Have Been Published in the Following Journal Articles -- 1 Introduction -- 1.1 Brief History of Semiconductors in Communication -- 1.2 Layout of this Dissertation -- References -- 2 Polarization-Induced 2D Hole Gases in Undoped (In)GaN/AlN Heterostructures -- 2.1 Introduction -- 2.2 Polarization Charges in III- Nitride Heterostructures -- 2.3 The Undoped GaN/AlN 2DHG -- 2.4 Impurity Blocking Layers in the AlN Buffer Layer -- 2.5 Very High density InGaN/AlN 2DHGs -- 2.6 Conclusions -- 2.7 Future Directions -- References -- 3 GHz-Speed GaN/AlN p-channel Heterojunction Field Effect Transistors -- 3.1 Introduction -- 3.2 Current Challenges for GaN pFETs -- 3.3 Mg-InGaN Ohmic Contacts to GaN/AlN 2DHG -- 3.4 Scaled RF GaN/AlN p-channel FETs -- 3.5 Benchmark -- 3.6 Future Directions -- References -- 4 Polarization-Induced 2D Electron and Holes in Undoped AlN/GaN/AlN Heterostructures -- 4.1 Introduction -- 4.2 The AlN/GaN/AlN Heterostructure -- 4.3 The Undoped 2D Electron-Hole Bilayer -- 4.4 AlN/GaN/AlN 2DEGs for High-Power RF HEMTs -- 4.4.1 Low-Field Transport -- 4.4.2 High-Field Velocities -- 4.4.3 Shubnikov-de-Haas Oscillations -- 4.5 Future Directions -- References -- 5 AlN/GaN/AlN High Electron Mobility Transistors -- 5.1 Introduction -- 5.2 Thermal Advantage of AlN Buffer Layer -- 5.3 MBE- Grown AlN Buffer Layers on SiC for RF HEMTs -- 5.4 State-of-Art

AlN/GaN/AlN HEMTs -- 5.5 In-situ AlN Passivation for Reduced Dispersion -- 5.5.1 GaN Channel Strain in AlN/GaN/AlN Heterostructures -- 5.5.2 2DEG Transport in In-situ Passivated AlN/GaN/AlN Heterostructures -- 5.5.3 Reduced Dispersion in AlN/GaN/AlN HEMTs -- 5.6 Enhancement-Mode AlN/GaN/AlN MOS-HEMTs with Ultra-Thin 3nm GaN Channels -- 5.7 Future Directions -- References.

6 Integrated RF Electronics on the AlN Platform -- 6.1 Introduction -- 6.2 Survey of GaN-Based CMOS-Logic Realizations -- 6.3 AlN-Based CMOS Realizations -- 6.4 In-situ Sublimation Etch of GaN -- 6.5 Passive RF Devices on AlN Platform -- 6.5.1 Epitaxial AlN Bulk Acoustic Waveguide Resonators -- 6.5.2 SiC Substrate Integrated Waveguides (SIW) -- References -- 7 Epitaxial Growth of AlN-Based Heterostructures for Electronics -- 7.1 PA-MBE Growth of GaN/AlN 2DHGs -- 7.1.1 Detailed Growth Recipe -- 7.1.2 Variations in the 2DHG Active Region -- 7.1.3 Growth Condition Optimization Studies -- Optimizing the GaN/AlN Interface -- Large Area Growths -- 7.2 PA-MBE Growth of AlN/GaN/AlN 2DEGs -- 7.2.1 In-situ Cleaning of 6H-SiC -- 7.2.2 Detailed Growth Recipe -- 7.2.3 In-situ AlN passivated AlN/GaN/AlN HEMTs -- References -- 8 Electronics on Single-Crystal, Bulk AlN Substrates -- 8.1 Single-Crystal AlN Substrates for Transistors -- 8.2 Early Results -- References -- A Author's Biographical Sketch.
